S8550 TRANSISTOR (PNP)

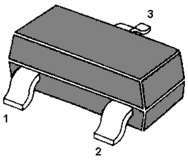
FEATURES

Complimentary to S8050

Collector current: I_C=0.5A

MARKING : 2TY

SOT-23



1. BASE
2. EMITTER
3. COLLECTOR

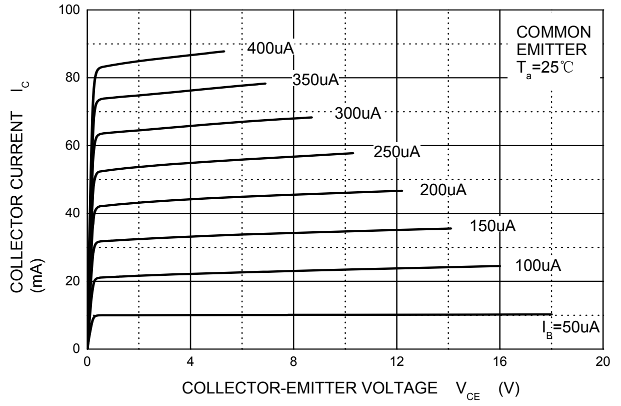
MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

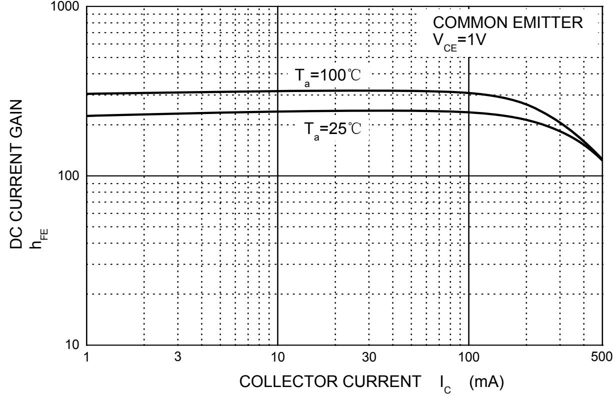
Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-0.5	A
P_C	Collector Power Dissipation	0.3	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

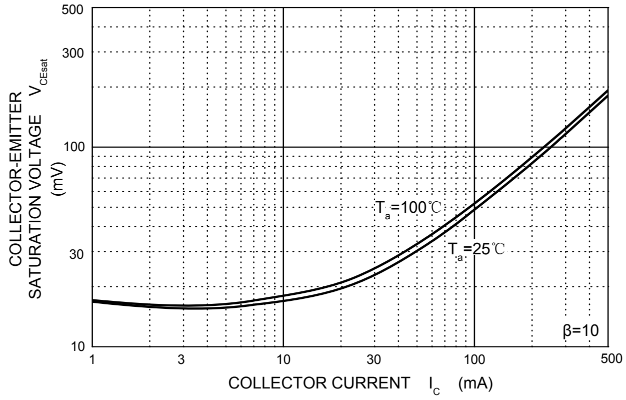
ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

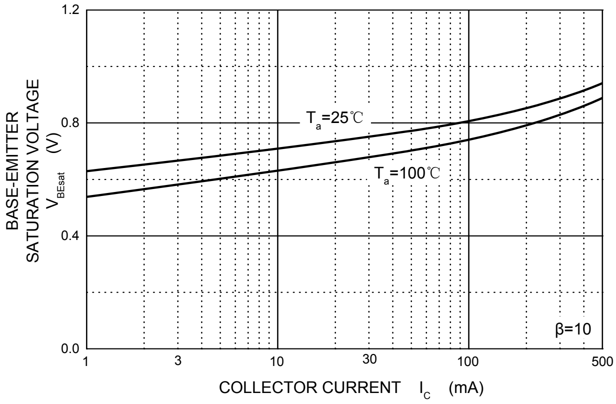
Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C = -100μA, I_E=0	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C =-1mA, I_B=0	-25		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E= -100μA, I_C=0	-5		V
Collector cut-off current	I_{CBO}	V_{CB}= -40V, I_E=0		-0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}= -20V, I_B=0		-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= -3V, I_C=0		-0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}= -1V, I_C= -50mA	200	350	
	$h_{FE(2)}$	V_{CE}= -1V, I_C= -500mA	50		
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=-500mA, I_B= -50mA		-0.6	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C=-500mA, I_B= -50mA		-1.2	V
Transition frequency	f_T	V_{CE}= -6V, I_C= -20mA f=30MHz	150		MHz

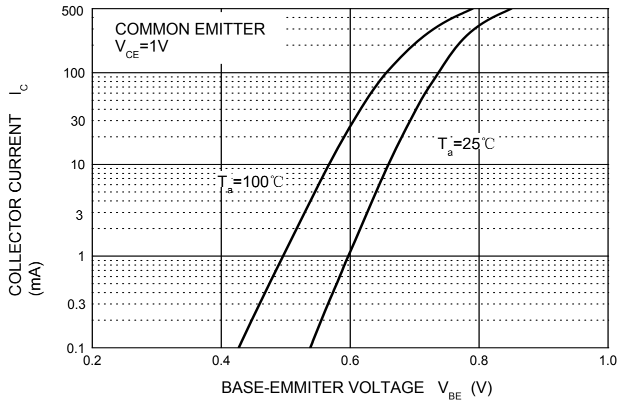
Typical Characteristics

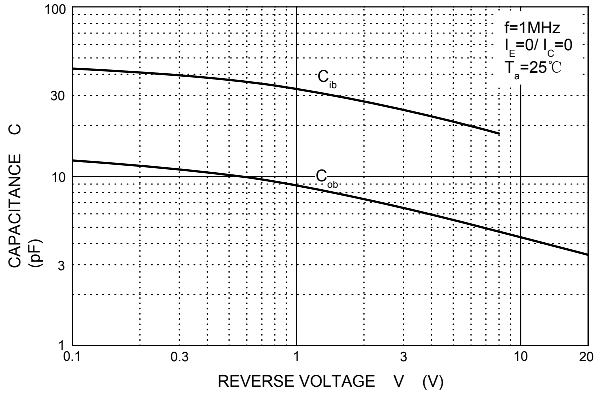

Static Characteristic

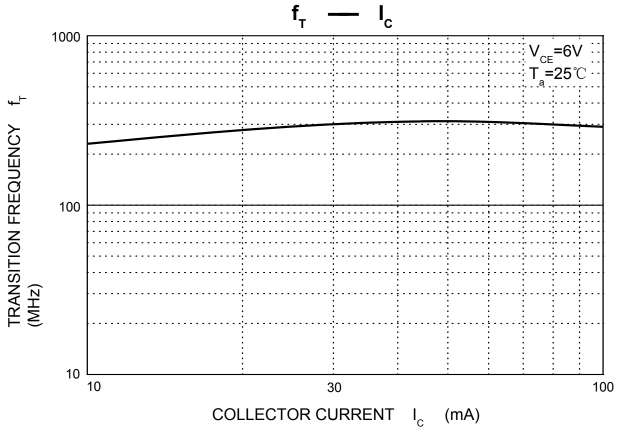

h_{FE} — I_C

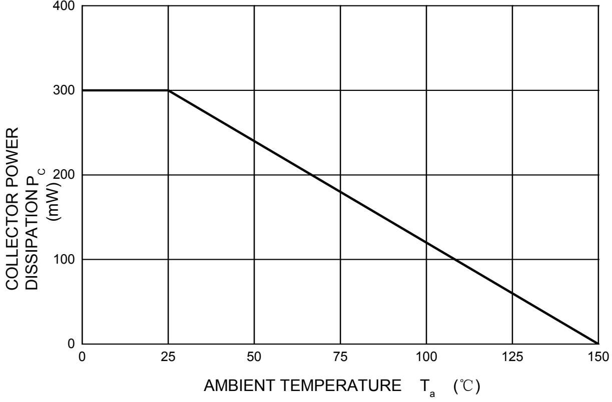

V_{CEsat} — I_C


V_{BEsat} — I_C


I_C — V_{BE}

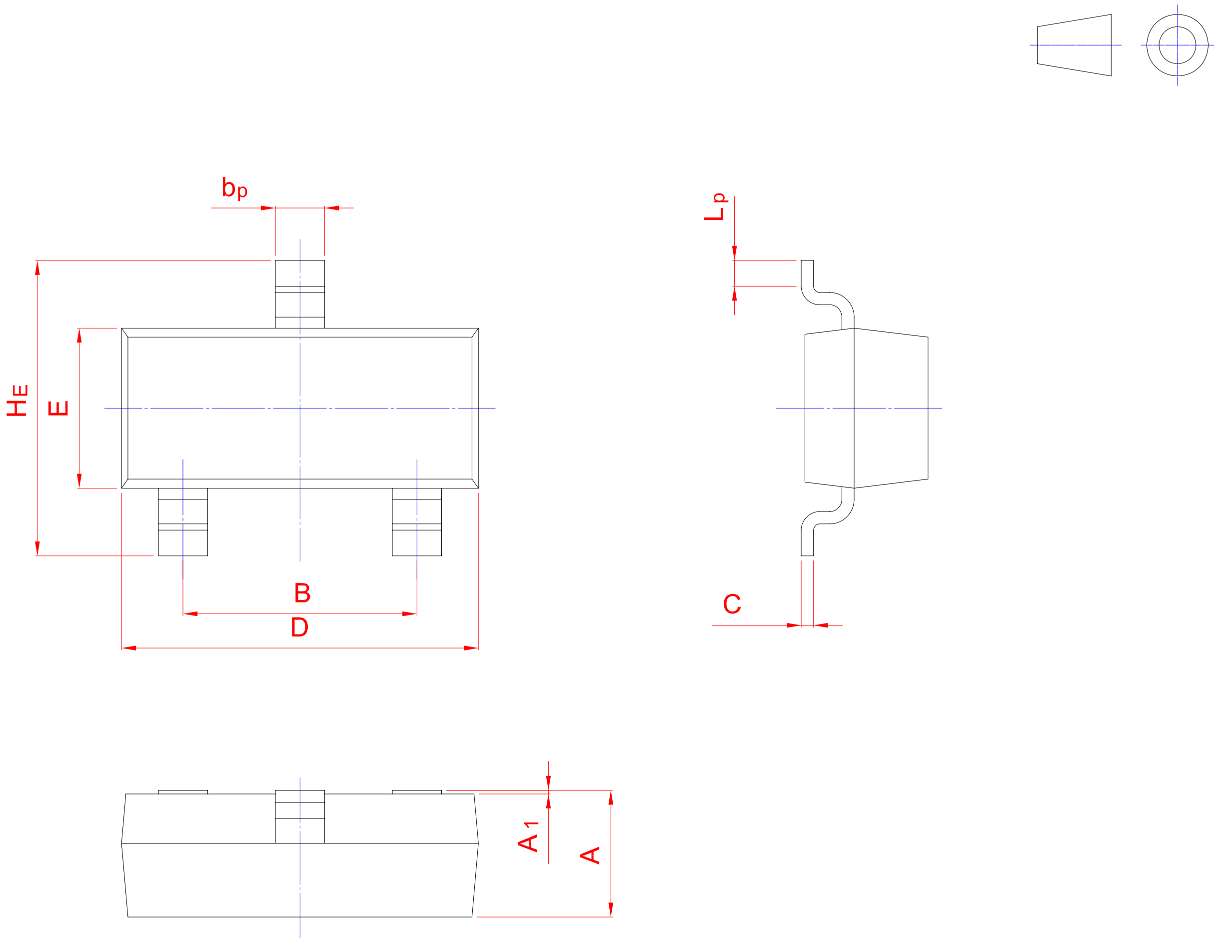

C_{ob}/ C_{ib} — V_{CB}/ V_{EB}


f_T — I_C


P_C — T_a

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads **SOT-23**



UNIT	A	B	b_p	C	D	E	H_E	A_1	L_p
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20